
2SD1163, 2SD1163A

Silicon NPN Triple Diffused

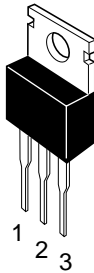
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Application

TV horizontal deflection output

Outline

TO-220AB



1. Base
2. Collector
(Flange)
3. Emitter

2SD1163, 2SD1163A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating			Unit
		2SD1163	2SD1163A		
Collector to base voltage	V_{CBO}	300	350		V
Collector to emitter voltage	V_{CEO}	120	150		V
Emitter to base voltage	V_{EBO}	6	6		V
Collector current	I_C	7	7		A
Collector peak current	$I_{C(peak)}$	10	10		A
Collector surge current	$I_{C(surge)}$	20	20		A
Collector power dissipation	P_C^{*1}	40	40		W
Junction temperature	T_j	150	150		°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150		°C

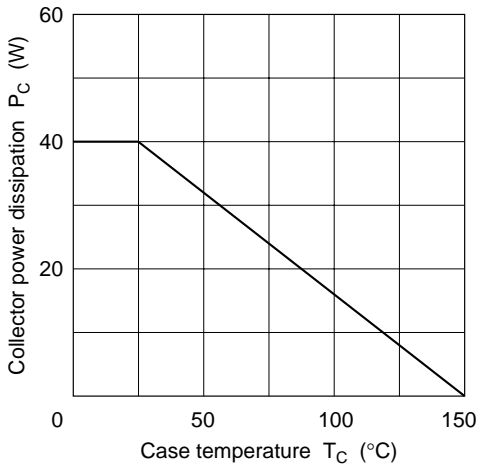
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

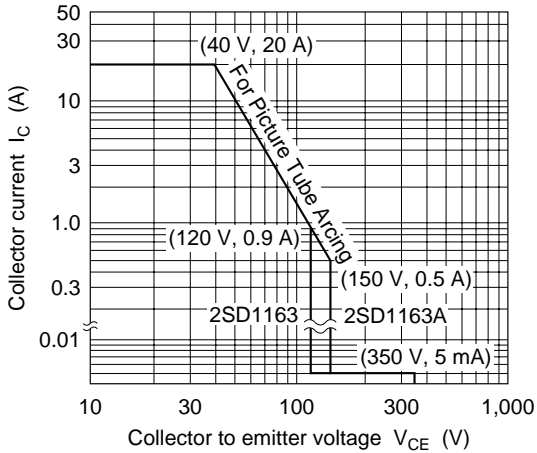
Item	Symbol	2SD1163			2SD1163A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector cutoff current	I_{CBO}	—	—	5	—	—	—	mA	$V_{CB} = 300\text{ V}, I_E = 0$
		—	—	—	—	—	5	mA	$V_{CB} = 350\text{ V}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	150	—	—	V	$I_C = 10\text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	6	—	—	V	$I_E = 10\text{ mA}, I_C = 0$
DC current transfer ratio	h_{FE}	25	—	—	25	—	—		$V_{CE} = 5\text{ V}, I_C = 5\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2.0	—	—	1.0	V	$I_C = 5\text{ A}, I_B = 0.5\text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.2	—	—	1.2	V	$I_C = 5\text{ A}, I_B = 0.5\text{ A}^{*1}$
Fall time	t_f	—	—	0.5	—	—	0.5	μs	$I_{CP} = 3.5\text{ A}, I_{B1} = 0.45\text{ A}$

Note: 1. Pulse test.

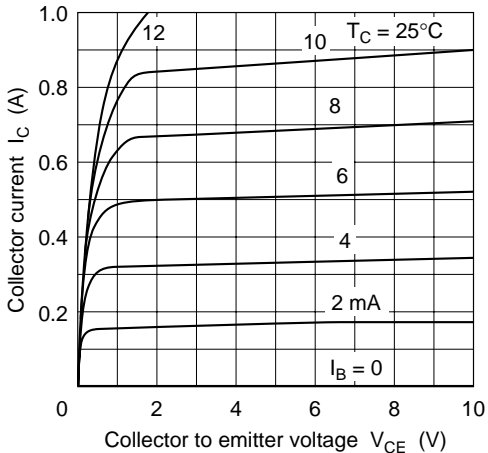
Maximum Collector Dissipation Curve



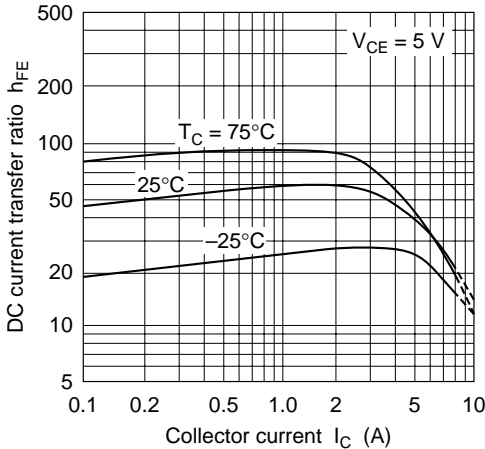
Area of Safe Operation

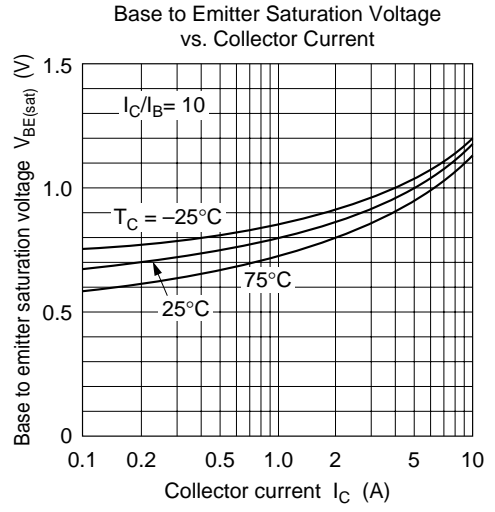
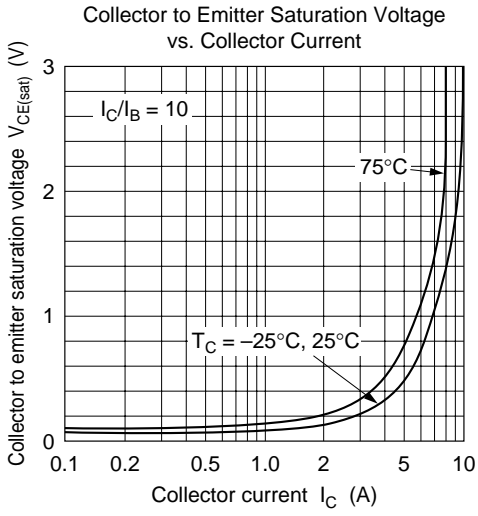


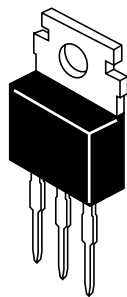
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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